

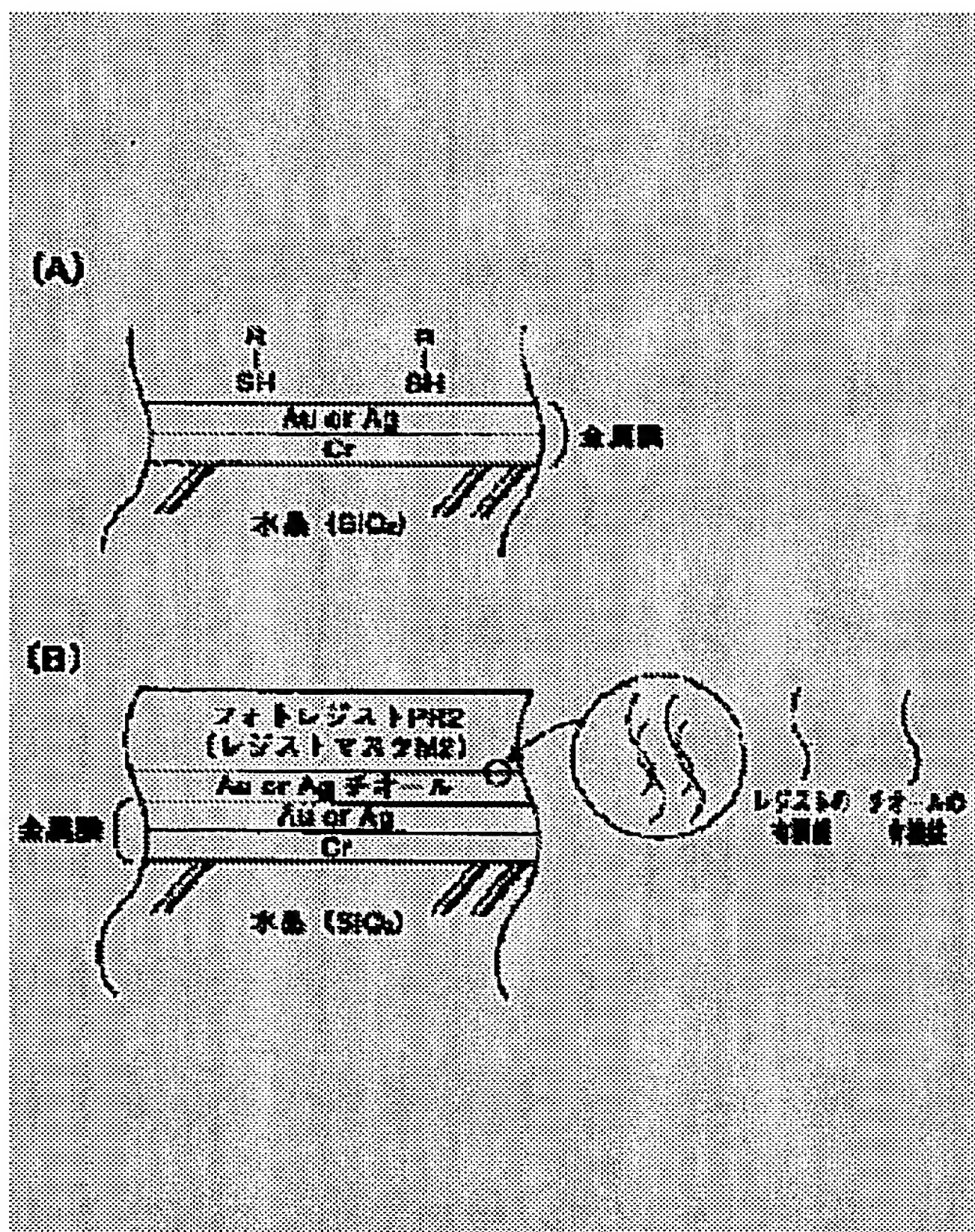
RESIST FILM FORMING METHOD AND RESIST

Patent number: JP11174683
Publication date: 1999-07-02
Inventor: NAKAGAWA TETSUO
Applicant: SEIKO EPSON CORP
Classification:
- international: G03F7/085; B05D3/00; C09D7/12; H01L21/027; H01L41/22; H03H3/02
- european:
Application number: JP19970346921 19971216
Priority number(s): JP19970346921 19971216

Report a data error here

Abstract of JP11174683

PROBLEM TO BE SOLVED: To enhance the adhesiveness of a resist film to base thereof by adhering thiol to a surface to be formed with a resist film, then applying the liquid resist to the surface. **SOLUTION:** A piezoelectric element piece formed with an electrode film forming metal film (a gold layer Au and a chromium layer Cr) is dipped in a treatment solution obtained by dissolving thiol with a solvent such as alcohol or ketone. Thiol is expressed by R-SH (R is an organic group such as an alkyl group or the like and desirably, an alkyl group having three or more carbon atoms). Photoresist PR2 is applied to a surface of the gold layer Au through the thiol later, and the thiol layer is interposed between the surface of the gold layer Au and the photoresist PR2 (resist mask M2). Since adhesiveness of the surface of the gold layer Au to the photo resist PR2 is strung, peeling of the resist film from the gold layer Au and intrusion of etching liquid between the surface of the gold layer Au and the resist mask Ms are prevented.



Data supplied from the esp@cenet database - Worldwide

BEST AVAILABLE COPY